Complementary Power Transistors

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("1" Suffix)
- Electrically Similar to Popular TIP41 and TIP42 Series
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V _{CEO}	100	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current – Continuous	I _C	6	Adc
Collector Current – Peak	I _{CM}	10	Adc
Base Current	Ι _Β	2	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	20 0.16	W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

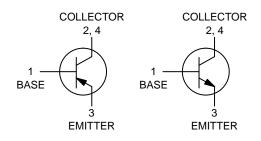


ON Semiconductor®

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SILICON POWER TRANSISTORS 6 AMPERES 100 VOLTS, 20 WATTS

COMPLEMENTARY



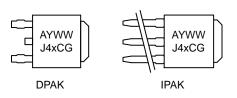


DPAK CASE 369C STYLE 1



IPAK CASE 369D STYLE 1

MARKING DIAGRAMS



A = Assembly Location

= Year

WW = Work Week J4xC = Device Code

x = 1 or 2

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

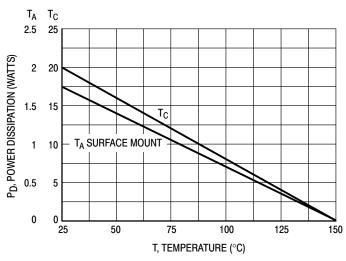
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	1		<u> </u>	1
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 30 mAdc, I _B = 0)	V _{CEO(sus)}	100	_	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, I _B = 0)	ICEO	_	50	μAdc
Collector Cutoff Current (V _{CE} = 100 Vdc, V _{EB} = 0)	I _{CES}	_	10	μAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	0.5	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain $ (I_C = 0.3 \text{ Adc, } V_{CE} = 4 \text{ Vdc}) $ $ (I_C = 3 \text{ Adc, } V_{CE} = 4 \text{ Vdc}) $	h _{FE}	30 15	- 75	_
Collector–Emitter Saturation Voltage (I _C = 6 Adc, I _B = 600 mAdc)	V _{CE(sat)}	_	1.5	Vdc
Base–Emitter On Voltage (I _C = 6 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	_	2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product (Note 4) (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1 MHz)	f _T	3	-	MHz
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1 kHz)	h _{fe}	20	_	_

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

4. $f_T = |h_{fe}| \bullet f_{test}$.

TYPICAL CHARACTERISTICS

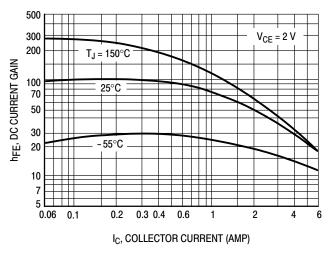


 V_{CC} +30 V R_{C} +11 V 0 -9 V t_{t} , $t_{t} \leq 10 \text{ ns}$ DUTY CYCLE = 1%

 R_B and R_C varied to obtain desired current levels D_1 must be fast recovery type, e.g.: MSB5300 USED ABOVE $I_B\approx 100$ mA MSD6100 USED BELOW $I_B\approx 100$ mA REVERSE ALL POLARITIES FOR PNP.

Figure 1. Power Derating

Figure 2. Switching Time Test Circuit



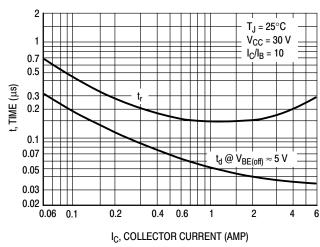
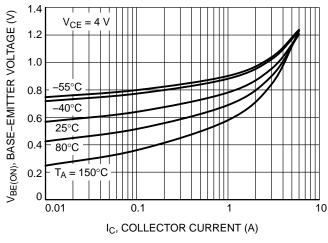


Figure 3. DC Current Gain

Figure 4. Turn-On Time



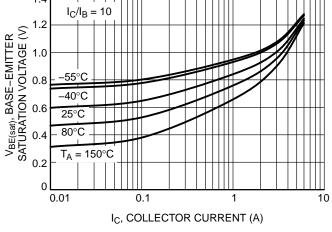


Figure 5. Base Emitter Voltage vs. Collector Current

Figure 6. Base Emitter Saturation Voltage vs.
Collector Current

TYPICAL CHARACTERISTICS

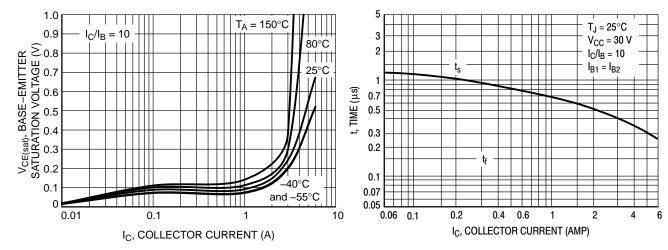


Figure 7. Collector Emitter Saturation Voltage vs. Collector Current

Figure 8. Turn-Off Time

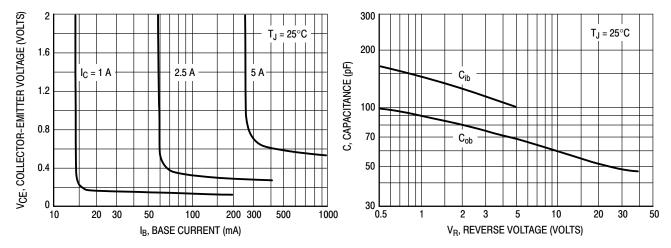


Figure 9. Collector Saturation Region

Figure 10. Capacitance

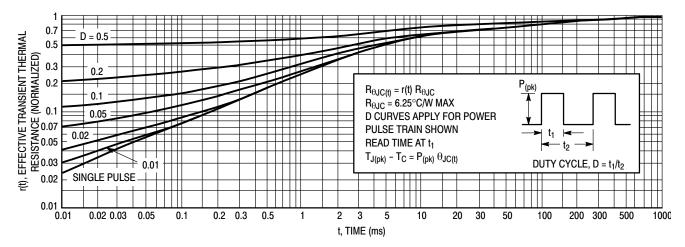


Figure 11. Thermal Response

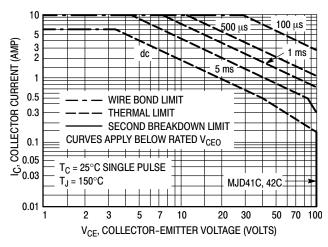


Figure 12. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 12 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 11. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MJD41CRLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD41CT4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD41CT4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD42CG	DPAK (Pb-Free)	369C	75 Units / Rail
MJD42C1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD42CRLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
NJVMJD42CRLG*	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD42CT4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD42CT4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure. BRD8011/D.

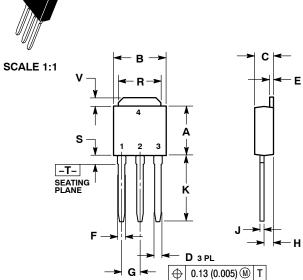
^{*}NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MECHANICAL CASE OUTLINE





DATE 15 DEC 2010



STYLE 2:

PIN 1. GATE

3

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

2. DRAIN

4. DRAIN

MT2

SOURCE

STYLE 3: PIN 1. ANODE

2. CATHODE

4. CATHODE

3 ANODE

STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER

COLLECTOR

STYLE 1: PIN 1. BASE

3

STYLE 5: PIN 1. GATE

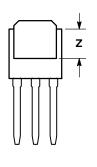
2. ANODE 3. CATHODE

ANODE

2. COLLECTOR

EMITTER

COLLECTOR



NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

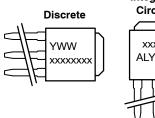
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
7	0.155		3 93	

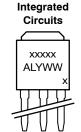
MARKING DIAGRAMS

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

YWW

XXXXXXXXX





xxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

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DETAIL A ROTATED 90° CW

STYLE 2:

STYLE 1:

DPAK (SINGLE GAUGE) CASE 369C **ISSUE F**

DATE 21 JUL 2015

NOTES:

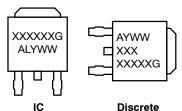
- IOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES. 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-

- MENSIONS b3, L3 and Z.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIM	IETERS
DIM	MIN	MIN MAX		MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	0.090 BSC		BSC
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code

= Assembly Location Α

L = Wafer Lot Υ = Year

WW = Work Week G = Pb-Free Package

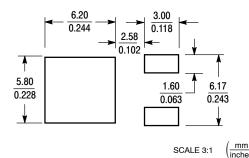
*This information is generic. Please refer to device data sheet for actual part marking.

SCALE 1:1 - h3 В L3 € DETAIL A NOTE 7 **BOTTOM VIEW** Ce SIDE VIEW | \oplus | 0.005 (0.13) lacktriangledown C **TOP VIEW** Z Ħ L2 GAUGE C SEATING **BOTTOM VIEW** Δ1 ALTERNATE CONSTRUCTIONS

PIN 1. BASE 2. COLLE 3. EMITTE 4. COLLE	ER 3. SOL	JIN 2. CA	THODE :	1. CATHODE 2. ANODE 3. GATE 4. ANODE	PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	3. ANODE	3. RESIS	IODE STOR ADJUST	STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 3:

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

STYLE 5:

STYLE 4:

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